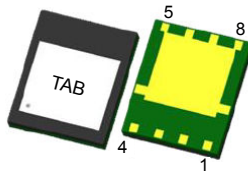
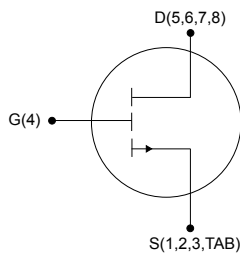


100 V, 1.1 mΩ typ., 501 A, e-mode PowerGaN transistor



En-FCLGA 5x6



G4D5678S123TAB



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D	Series
SGT1D5R10MEA	100 V	1.5 mΩ	501 A	G-HEMT

- Dual side cooling package
- Enhancement mode normally off transistor
- Extremely low capacitances
- High power management capability
- Very high switching speed
- Zero reverse recovery charge

Applications

- DC-DC converters
- Motor driver
- Solar system MPPT

Description

The SGT1D5R10MEA is a 100 V, 501 A e-mode PowerGaN transistor. The resulting device provides extremely low conduction losses, high current capability and ultra-fast switching operation to enable high power density and unbeatable efficiency performances.

Product status link

[SGT1D5R10MEA](#)

Product summary

Order code	SGT1D5R10MEA
Marking	1D5R10M
Package	En-FCLGA 5X6
Packing	Tape and reel

1 Electrical ratings

$T_C = 25\text{ °C}$ unless otherwise specified.

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
	Drain-source voltage (transient)	120	
V_{GS}	Gate-source voltage	-4 to 6	V
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	501	A
	Drain current (continuous) at $T_C = 100\text{ °C}$	317	
I_{DM}	Pulse drain current ($t_p = 100\text{ }\mu\text{s}$) at $T_C = 25\text{ °C}$	964	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ °C}$	735	W
T_{stg}	Storage temperature range	-40 to 150	°C
T_J	Operating junction temperature range		°C

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.17	°C/W
R_{thJA}	Thermal resistance, junction-to-ambient	38.1 ⁽¹⁾	°C/W

1. R_{thJA} is determined with the device on FR4 PCB (2s2p with thermal vias) defined in accordance with JEDEC standards. PCB is mounted in horizontal position without air stream cooling.

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified.

Table 3. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{DSS}	Drain-source leakage current	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}$		2.5	200	μA
		$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, T_J = 125\text{ °C}$		500		
I_{GSS}	Gate-source leakage current	$V_{DS} = 0\text{ V}, V_{GS} = 6\text{ V}$		2	200	μA
		$V_{DS} = 0\text{ V}, V_{GS} = 6\text{ V}, T_J = 125\text{ °C}$		50		
		$V_{DS} = 0\text{ V}, V_{GS} = -4\text{ V}$		2	200	
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 19\text{ mA}$	0.9	1.1	2.1	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 5\text{ V}, I_D = 2.5\text{ A}$		1.1	1.5	m Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V}, f = 100\text{ kHz}$	-	2295	-	pF
C_{oss}	Output capacitance		-	959	-	pF
C_{rss}	Reverse transfer capacitance		-	14	-	pF
$C_{o(er)}^{(1)}$	Equivalent output capacitance energy related	$V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V}, f = 100\text{ kHz}$	-	1367	-	pF
$C_{o(tr)}^{(2)}$	Equivalent output capacitance time related		-	1803	-	pF
R_g	Intrinsic gate resistance	$f = 5\text{ MHz}, I_D = 0\text{ A}$	-	0.76	-	Ω
V_{plat}	Gate plateau voltage	$V_{DS} = 50\text{ V}, I_D = 50\text{ A}$	-	1.6	-	V
Q_g	Total gate charge	$V_{DS} = 50\text{ V}, I_D = 50\text{ A}, V_{GS} = 0\text{ to }5\text{ V}$	-	15.9	-	nC
Q_{gs}	Gate-source charge		-	3.7	-	nC
Q_{gd}	Gate-drain charge		-	3.1	-	nC
Q_{rr}	Reverse recovery charge	$V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V}$	-	0	-	nC
Q_{oss}	Output charge		-	100	-	nC

- $C_{o(er)}$ is a constant capacitance value that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to the stated value.
- $C_{o(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to the stated value.

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{GS} = 5\text{ V}, V_{DD} = 50\text{ V},$ $I_D = 25\text{ A}, R_{G(off)} = 2\text{ }\Omega, R_{G(on)} = 10\text{ }\Omega,$ $L = 170\text{ }\mu\text{H}$	-	8.2	-	ns
t_r	Rise time		-	7.9	-	ns
$t_{d(off)}$	Turn-off delay time		-	15.7	-	ns
t_f	Fall time		-	7.6	-	ns

Table 6. Reverse conduction

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{SD}	Source-drain reverse voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 50\text{ A}$	-	2	-	V

2.1 Electrical characteristics (curves)

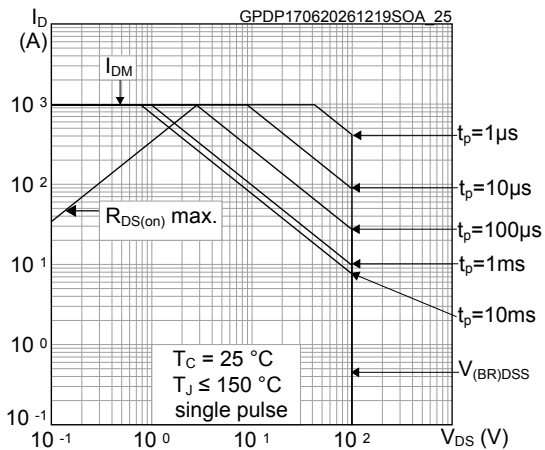
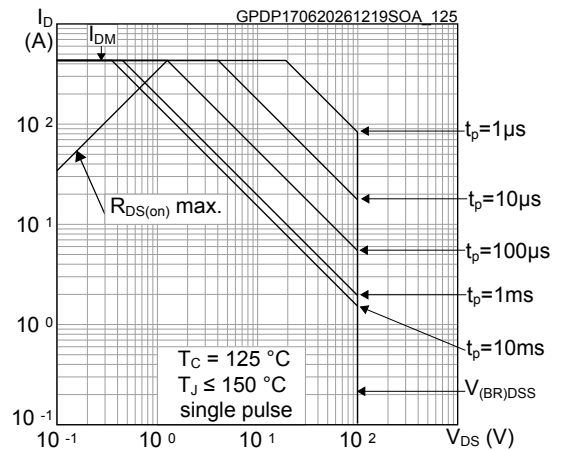
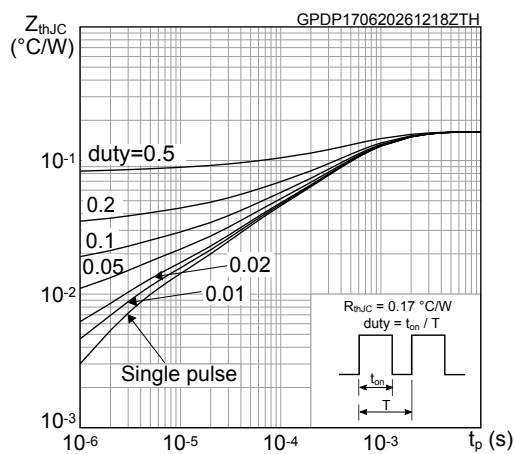
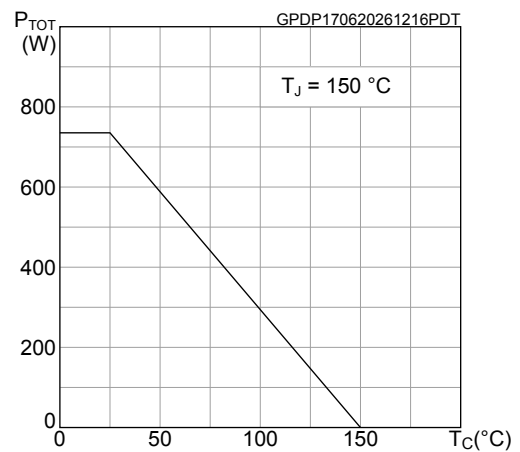
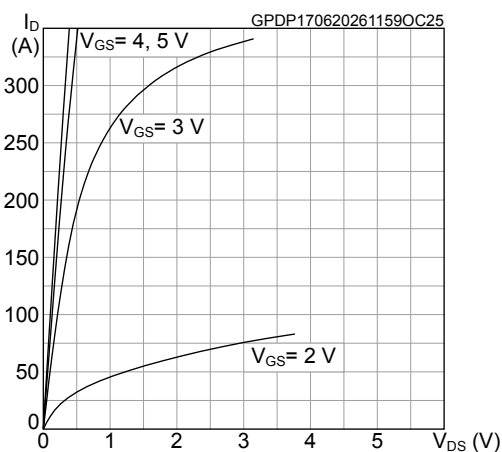
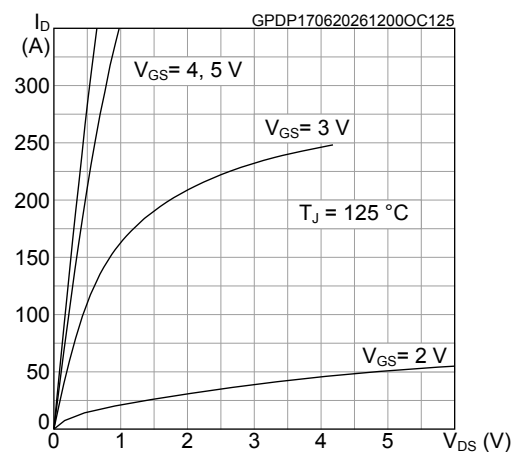
Figure 1. Safe operating area ($T_C = 25^\circ\text{C}$)

Figure 2. Safe operating area ($T_C = 125^\circ\text{C}$)

Figure 3. Maximum transient thermal impedance

Figure 4. Total power dissipation

Figure 5. Typical output characteristics ($T_J = 25^\circ\text{C}$)

Figure 6. Typical output characteristics ($T_J = 125^\circ\text{C}$)


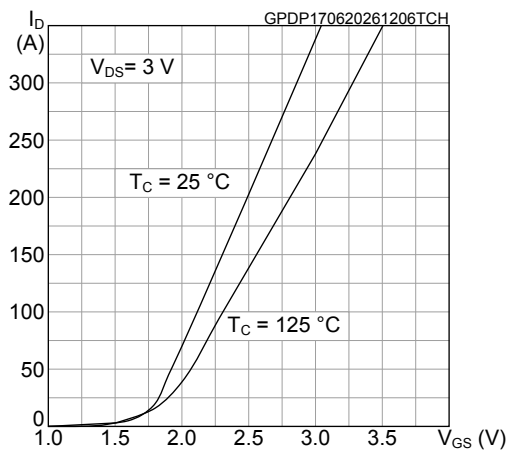
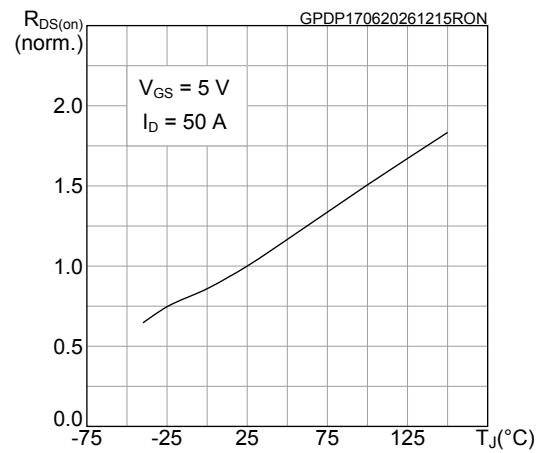
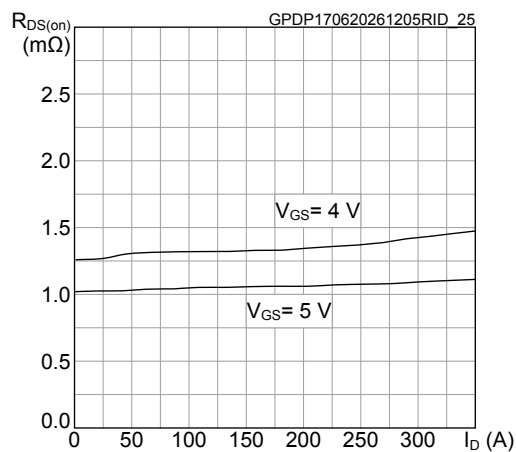
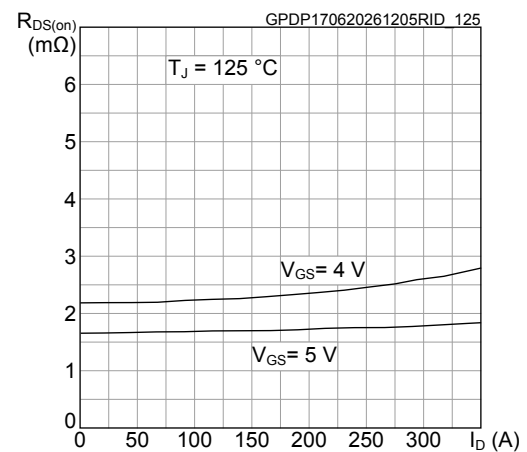
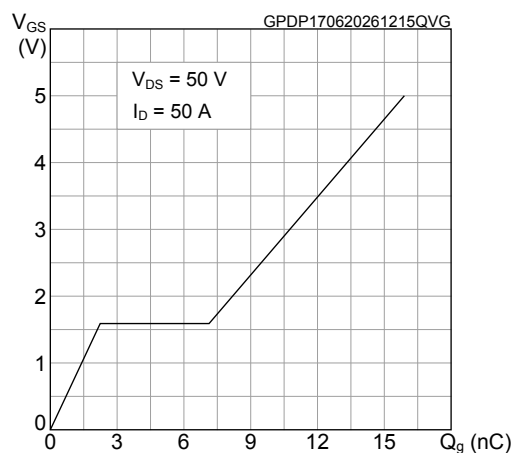
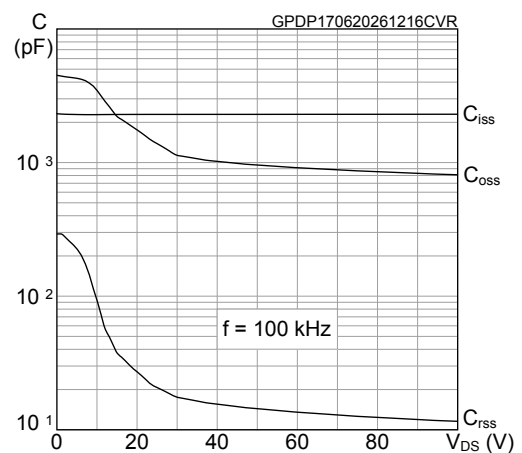
Figure 7. Typical transfer characteristics

Figure 8. Normalized on-resistance vs temperature

Figure 9. Typical drain-source on-resistance ($T_J = 25 \text{ }^{\circ}\text{C}$)

Figure 10. Typical drain-source on-resistance ($T_J = 125 \text{ }^{\circ}\text{C}$)

Figure 11. Typical gate charge characteristics

Figure 12. Typical capacitance characteristics


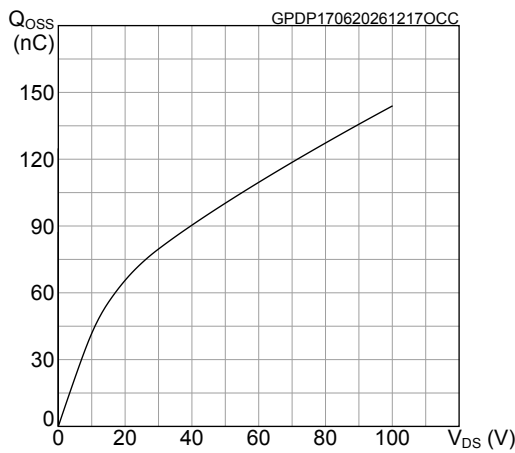
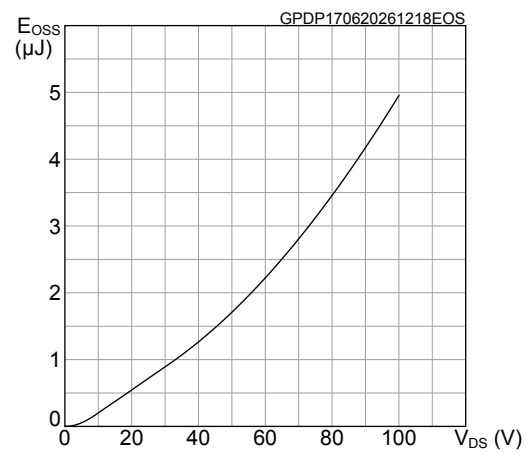
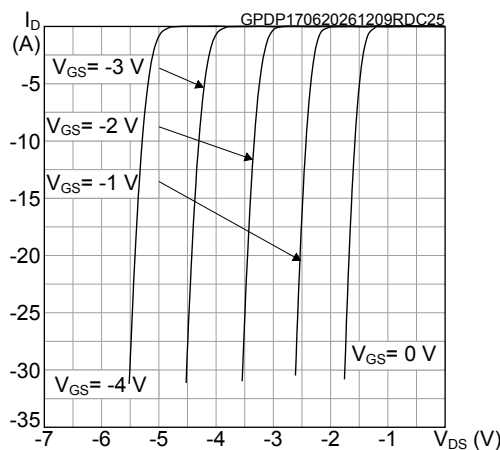
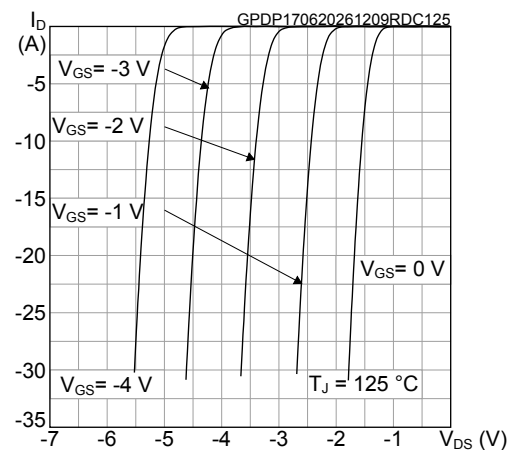
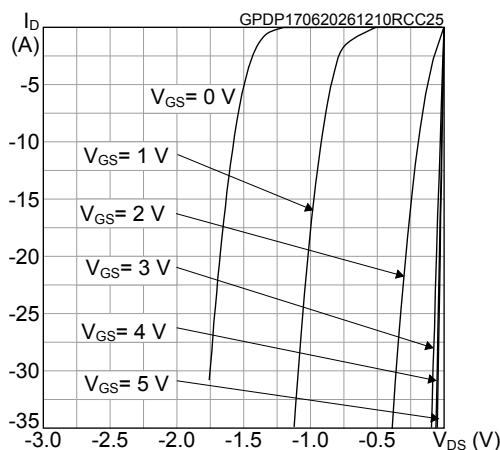
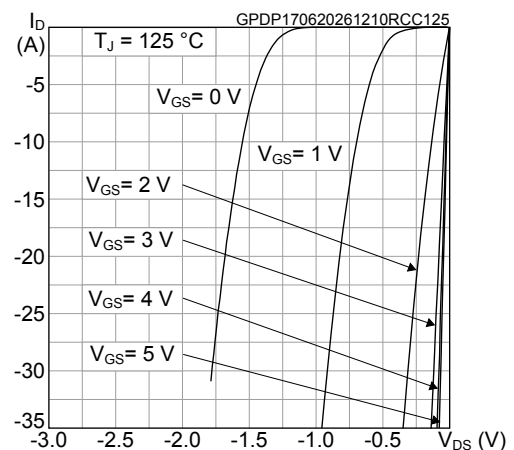
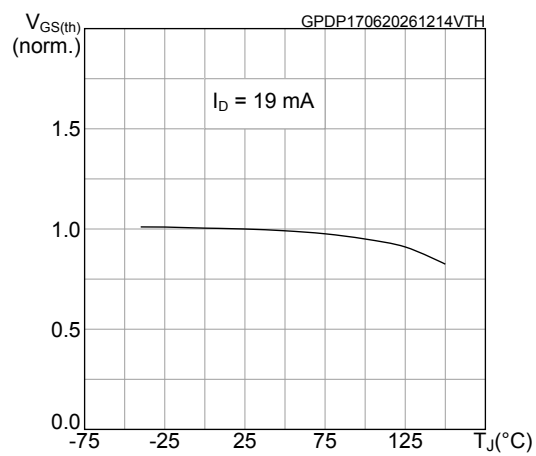
Figure 13. Typical output capacitance charge

Figure 14. Typical output capacitance stored energy

Figure 15. Typical diode reverse conduction characteristics ($T_J = 25^\circ\text{C}$)

Figure 16. Typical diode reverse conduction characteristics ($T_J = 125^\circ\text{C}$)

Figure 17. Typical reverse conduction characteristics ($T_J = 25^\circ\text{C}$)

Figure 18. Typical reverse conduction characteristics ($T_J = 125^\circ\text{C}$)


Figure 19. Normalized gate threshold vs temperature



3 Test circuits

Figure 20. Test circuit for inductive load switching times

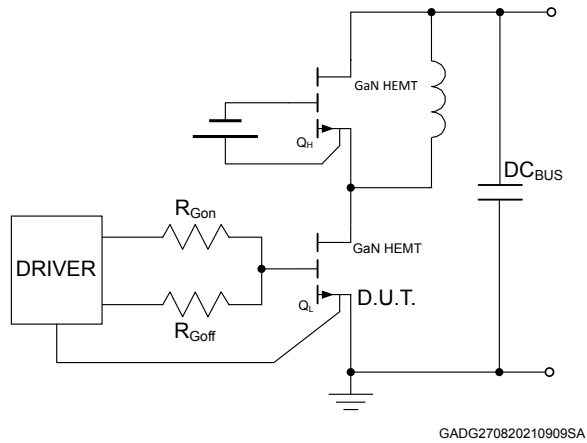
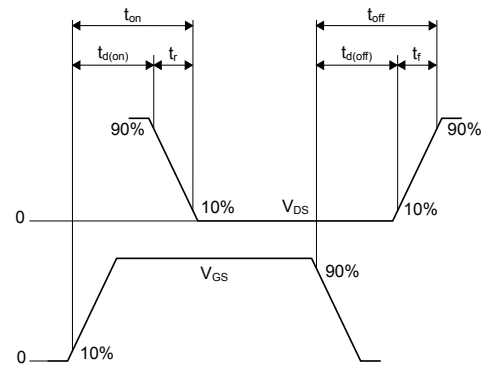


Figure 21. Switching time waveforms



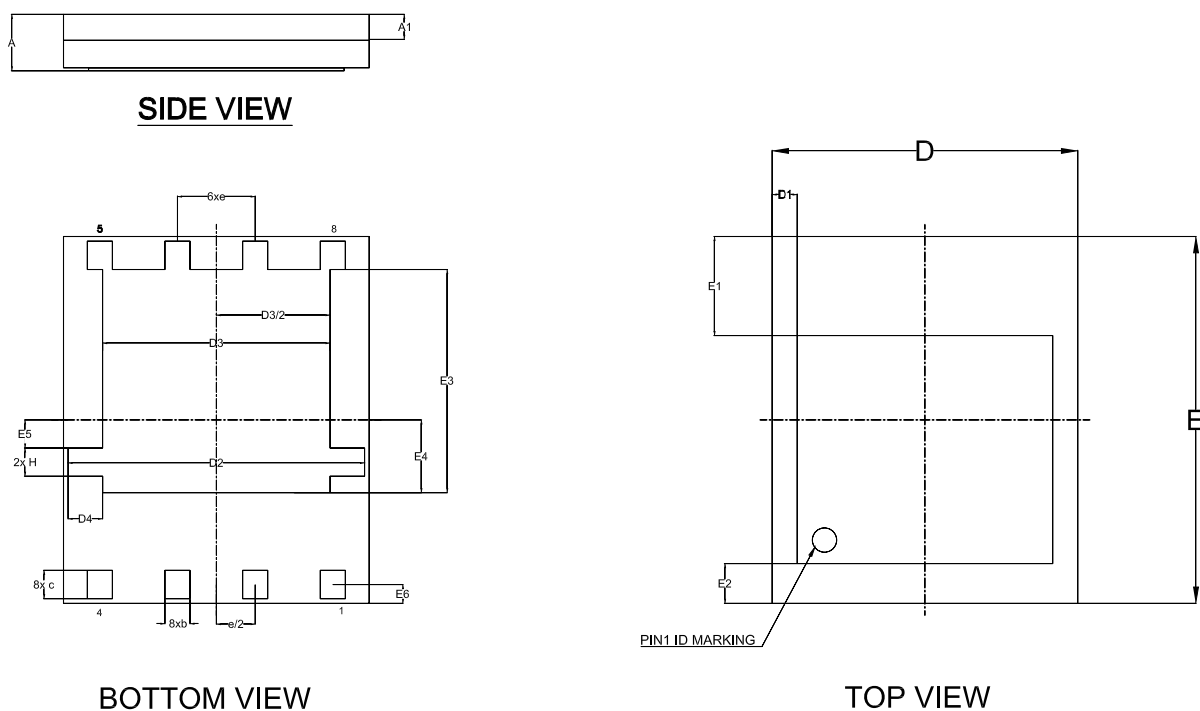
AM01473v1

4 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 En-FCLGA 5x6 package information

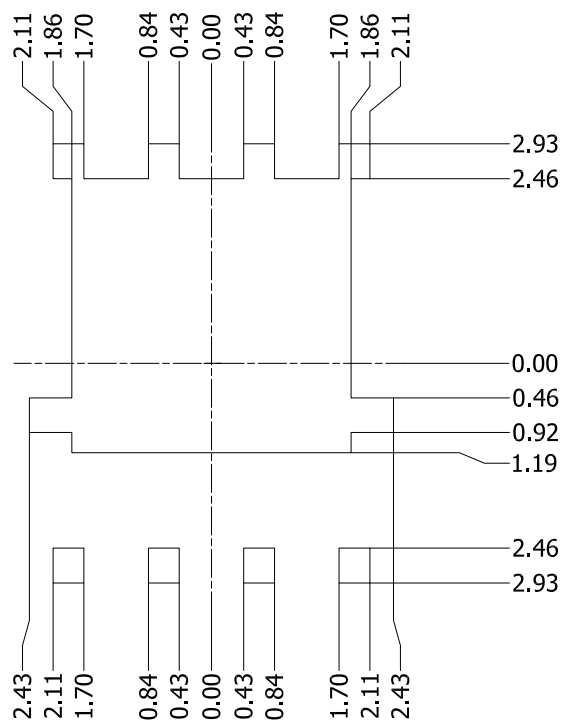
Figure 22. En-FCLGA 5x6 package outline



DM01190471_1

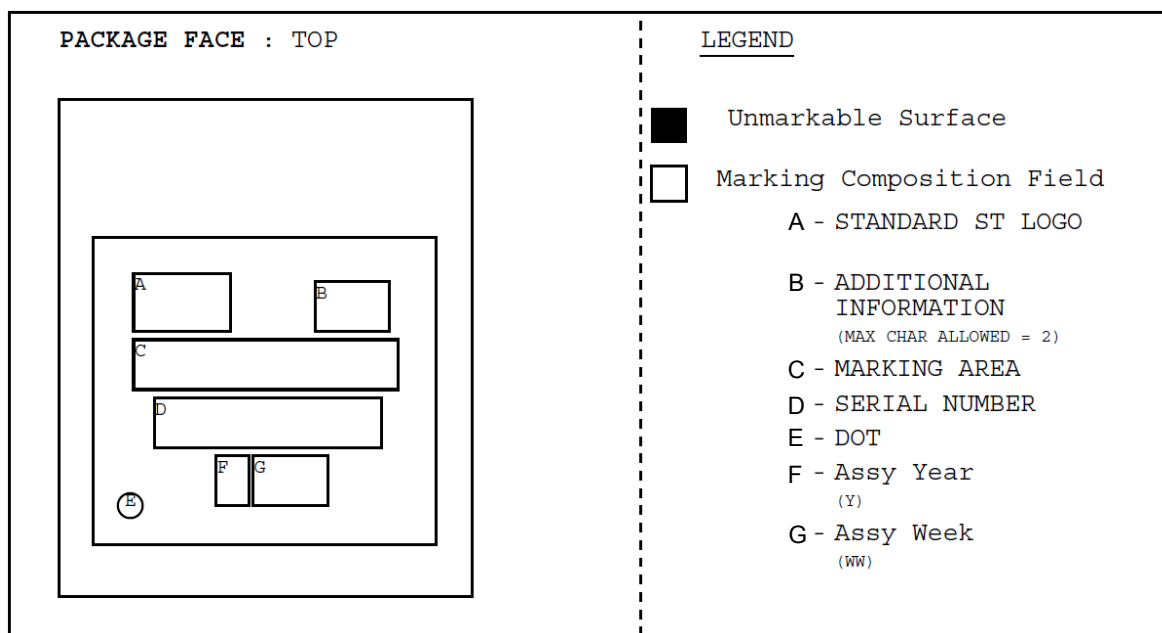
Table 7. En-FCLGA 5x6 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.774	0.874	0.974
A1	0.374	0.424	0.474
b	0.410 BSC		
c	0.415	0.465	0.515
D	4.900	5.000	5.100
D1	0.410 REF		
D2	4.850 REF		
D3	3.670	3.720	3.770
D4	0.515	0.565	0.615
E	5.900	6.000	6.100
E1	1.620 REF		
E2	0.650 REF		
E3	3.650 REF		
E4	1.190 REF		
E5	0.460 REF		
E6	0.310 REF		
e	1.270 BSC		
H	0.460 REF		

Figure 23. En-FCLGA 5x6 recommended footprint (dimensions are in mm)


DM01190471_1_footprint

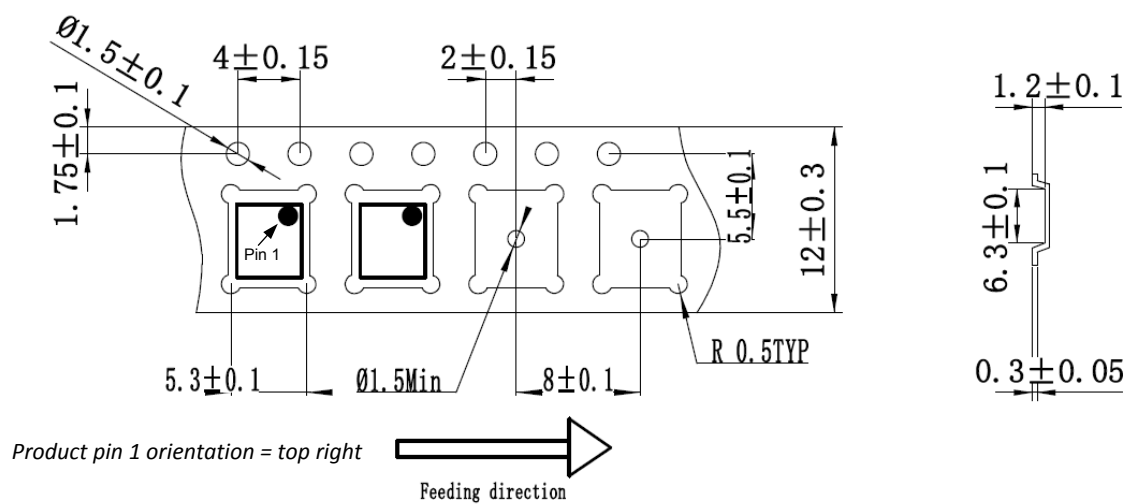
Figure 24. Marking composition for En-FCLGA 5x6



DM01224216_1_marking

4.2 En-FCLGA 5x6 packing information

Figure 25. En-FCLGA 5x6 tape drawing (dimensions are in mm)



DM01190544_1_tape

Revision history

Table 8. Document revision history

Date	Revision	Changes
03-Jul-2026	1	First release.

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